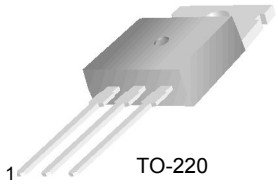
FAIRCHILD SEMICONDUCTOR®

October 2008

KSC5021
NPN Silicon Transistor

- High Voltage and High Reliability
- High Speed Switching : t_F = 0.1μs (Typ.)
- Wide SOA



TO-220

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	5	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	2	A
P_C	Collector Dissipation (T_C=25°C)	50	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

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Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 1mA, I_E = 0	800			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	500			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1mA, I_C = 0	7			V
V_{CEX}(sus)	Collector-Emitter Sustaining Voltage	I_C = 2.5A, I_{B1} = -I_{B2} = 1A L = 1mH, Clamped	500			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 500V, I_E = 0			10	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V, I_C = 0			10	μA
h_{FE1} h_{FE2}	DC Current Gain	V_{CE} = 5V, I_C = 0.6A V_{CE} = 5V, I_C = 3A	15 8		50	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 3A, I_B = 0.6A			1	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 3A, I_B = 0.6A			1.5	V
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0, f=1MHz		80		pF
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.6A		18		MHz
t_{ON}	Turn On Time	V_{CC} = 200V I_C = 5I_{B1} = -2.5I_{B2} = 4A R_L = 50Ω			0.5	μs
t_{STG}	Storage Time				3	μs
t_F	Fall Time				0.3	μs

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

h_{FE} Classification

Classification	R	O	Y
h_{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

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Typical Performance Characteristics

Figure 1. Static Characteristic

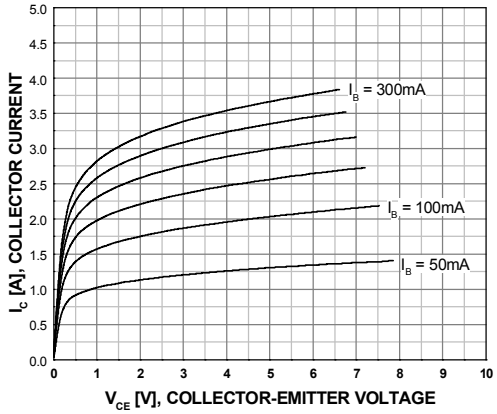


Figure 2. DC Current Gain (R-Grade)

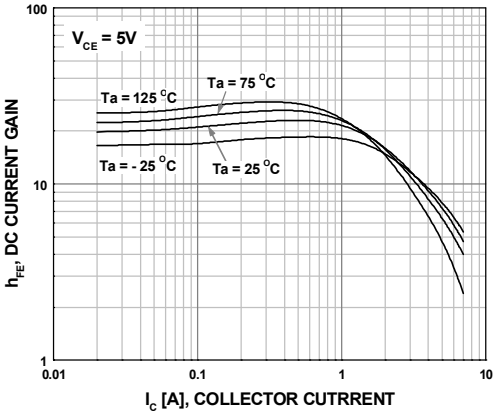


Figure 3. DC Current Gain (O-Grade)

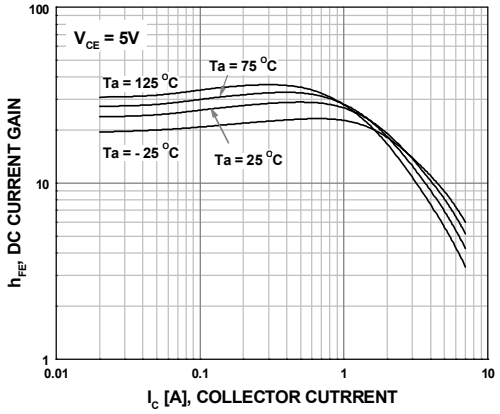


Figure 4. Saturation Voltage (R-Grade)

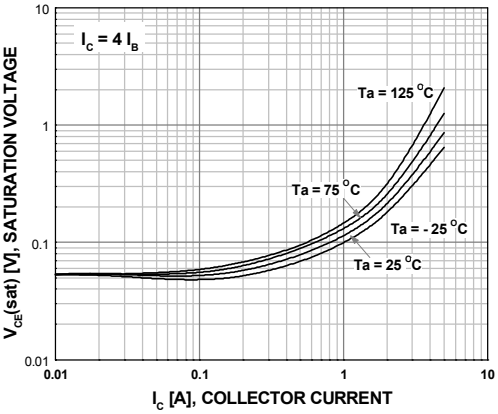


Figure 5. Saturatin Voltage (O-Grade)

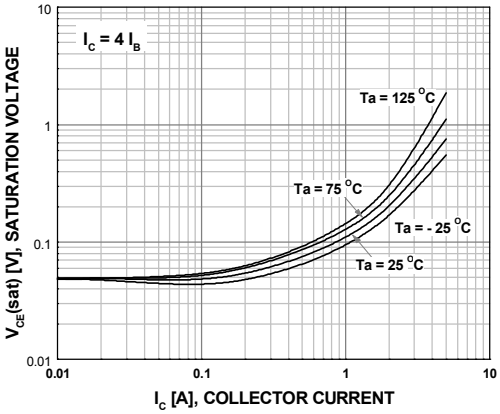
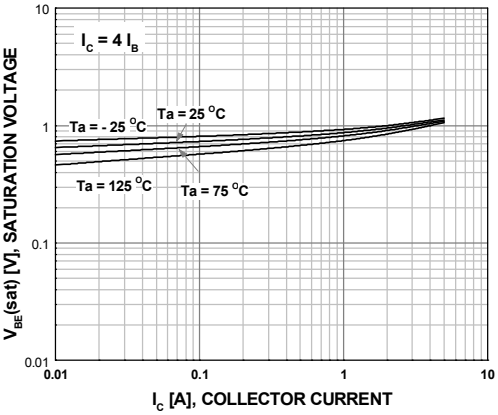


Figure 6. Saturation Voltage (R-Grade)



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Typical Characteristics

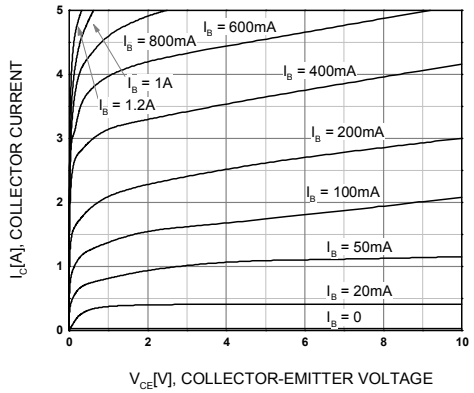

Figure 1. Static Characteristic

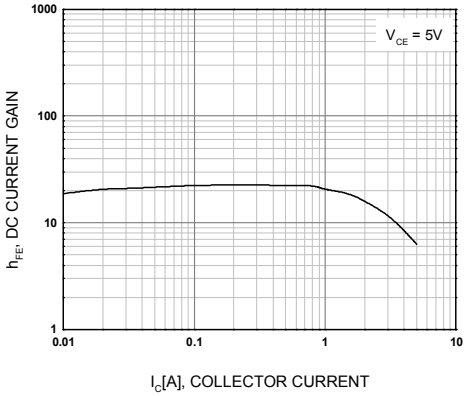

Figure 2. DC current Gain

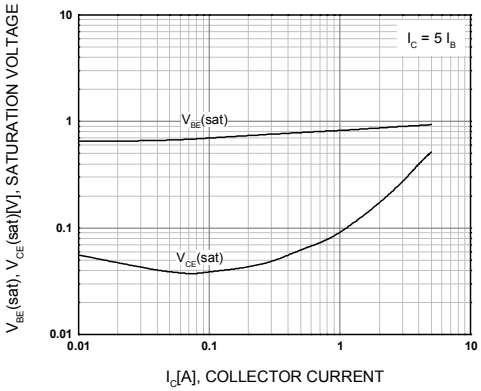

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

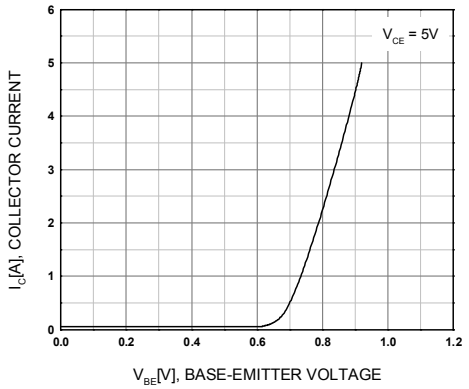

Figure 4. Base-Emitter On Voltage

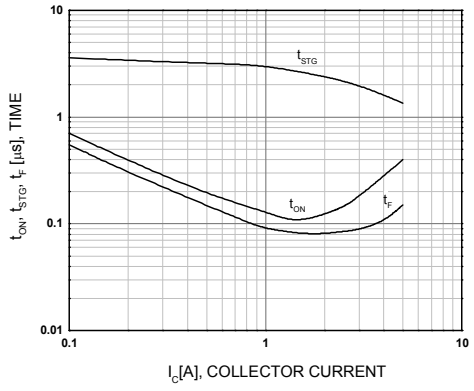

Figure 5. Switching Time

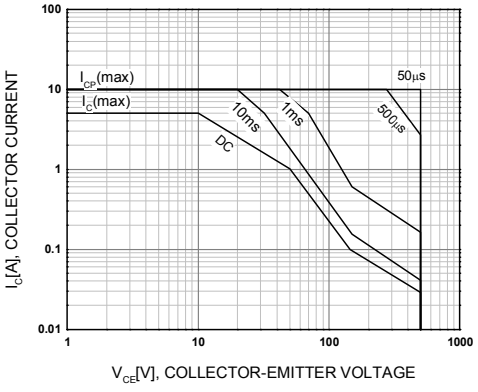

Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

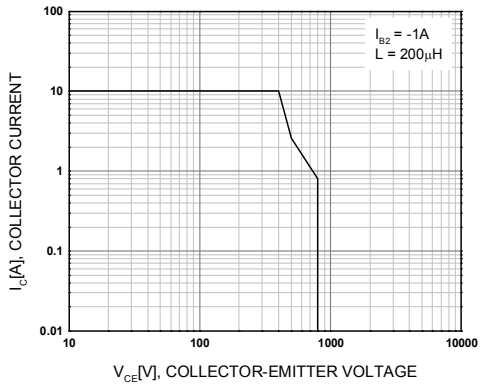


Figure 7. Reverse Bias Safe Operating Area

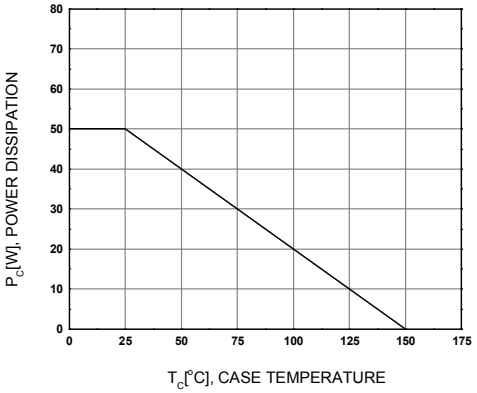
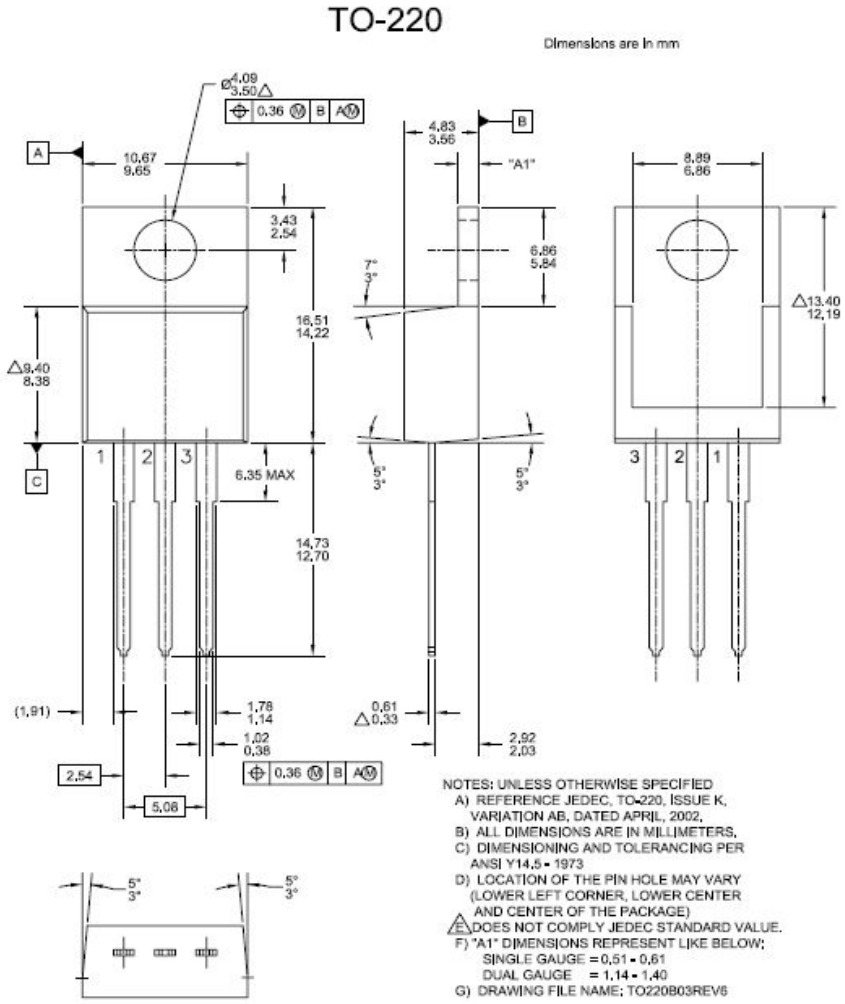


Figure 8. Power Derating

Package Dimension



Dimensions in Millimeters

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